

## RJP020N06T100-VB Datasheet

### N-Channel 60-V (D-S) MOSFET

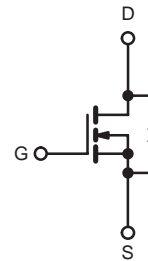
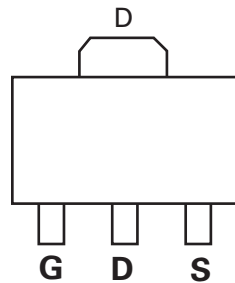
PRODUCT SUMMARY			
$V_{DS}$ (V)	$R_{DS(on)}$ ( $\Omega$ )	$I_D$ (A) <sup>a</sup>	$Q_g$ (Typ.)
60	0.076 at $V_{GS} = 10$ V	5.5	29 nC
	0.088 at $V_{GS} = 4.5$ V	4.5	

**FEATURES**

- Halogen-free
- TrenchFET<sup>®</sup> Power MOSFET

**APPLICATIONS**

- Load Switches for Portable Devices


**RoHS**  
 COMPLIANT


N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	$V_{DS}$	60	V	
Gate-Source Voltage	$V_{GS}$	$\pm 20$		
Continuous Drain Current ( $T_J = 150$ °C)	$I_D$	$T_C = 25$ °C	5.5 <sup>a</sup>	A
		$T_C = 70$ °C	4 <sup>a</sup>	
		$T_A = 25$ °C	4.7 <sup>a, b, c</sup>	
		$T_A = 70$ °C	4 <sup>a, b, c</sup>	
Pulsed Drain Current	$I_{DM}$	20		
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25$ °C	5.2	
		$T_A = 25$ °C	5.1 <sup>b, c</sup>	
Maximum Power Dissipation	$P_D$	$T_C = 25$ °C	5.3	W
		$T_C = 70$ °C	4	
		$T_A = 25$ °C	2.5 <sup>b, c</sup>	
		$T_A = 70$ °C	1.6 <sup>b, c</sup>	
Operating Junction and Storage Temperature Range	$T_J, T_{stg}$	- 55 to 150	°C	
Soldering Recommendations (Peak Temperature) <sup>e, f</sup>		260		

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>a, c, d</sup>	$R_{thJA}$	40	50	°C/W	
Maximum Junction-to-Foot (Drain)	$R_{thJF}$	15	20		

Notes:

a. Package limited,  $T_C = 25$  °C.

b. Surface Mounted on 1" x 1" FR4 board.

c.  $t = 10$  s.

d. Maximum under Steady State conditions is 95 °C/W.

e. See Reliability Manual for profile. The ChipFET is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.

f. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

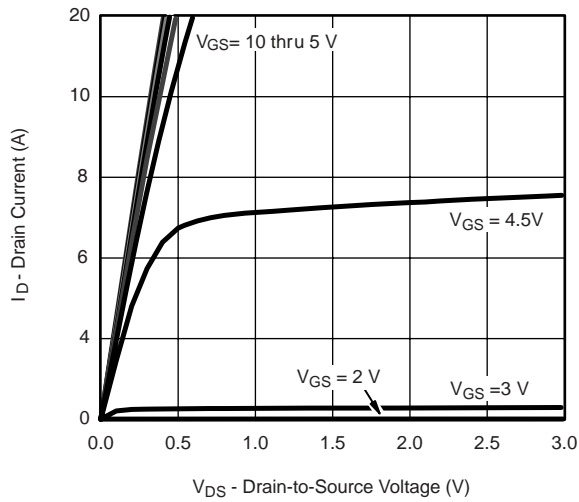
<b>SPECIFICATIONS</b> $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
$V_{DS}$ Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = 250\text{ }\mu\text{A}$		25		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			- 4.0		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	1.5		3.0	V
Gate-Source Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 12\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 60\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			10	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}, V_{GS} = 4.5\text{ V}$	25			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}, I_D = 3.3\text{ A}$		0.088		$\Omega$
		$V_{GS} = 10\text{ V}, I_D = 4.5\text{ A}$		0.076		
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 10\text{ V}, I_D = 4.3\text{ A}$		45		S
<b>Dynamic<sup>b</sup></b>						
Input Capacitance	$C_{iss}$	$V_{DS} = 10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		800		pF
Output Capacitance	$C_{oss}$			120		
Reverse Transfer Capacitance	$C_{rss}$			100		
Total Gate Charge	$Q_g$	$V_{DS} = 10\text{ V}, V_{GS} = 10\text{ V}, I_D = 6.3\text{ A}$		22	33	nC
				10	15	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 6.3\text{ A}$		2.5		
Gate-Drain Charge	$Q_{gd}$			1.7		
Gate Resistance	$R_g$	$f = 1\text{ MHz}$		2.4		$\Omega$
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 6.7\text{ A}, V_{GEN} = 4.5\text{ V}, R_g = 1\text{ }\Omega$		15	25	ns
Rise Time	$t_r$			10	15	
Turn-Off Delay Time	$t_{d(off)}$			35	55	
Fall Time	$t_f$			12	20	
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}, R_L = 1.5\text{ }\Omega$ $I_D \cong 6.7\text{ A}, V_{GEN} = 10\text{ V}, R_g = 1\text{ }\Omega$		10	15	
Rise Time	$t_r$			12	20	
Turn-Off Delay Time	$t_{d(off)}$			25	40	
Fall Time	$t_f$			10	15	
<b>Drain-Source Body Diode Characteristics</b>						
Continuous Source-Drain Diode Current	$I_S$	$T_C = 25\text{ }^\circ\text{C}$			7.2	A
Pulse Diode Forward Current	$I_{SM}$				25	
Body Diode Voltage	$V_{SD}$	$I_S = 6.7\text{ A}, V_{GS} = 0\text{ V}$		0.8	1.2	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 6.7\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		20	40	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$			10	20	nC
Reverse Recovery Fall Time	$t_a$			10		ns
Reverse Recovery Rise Time	$t_b$			10		

Notes:

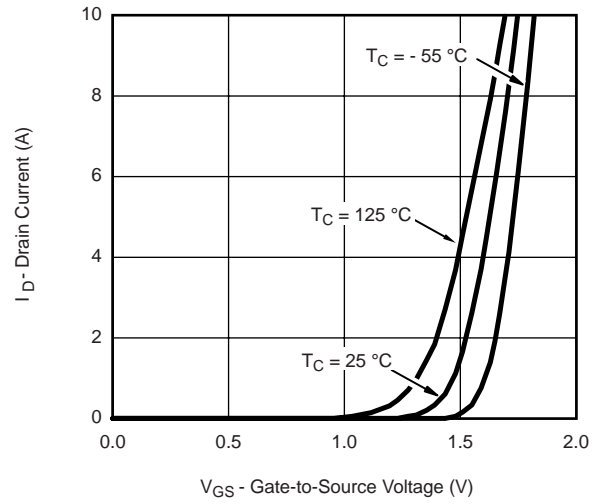
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$   
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

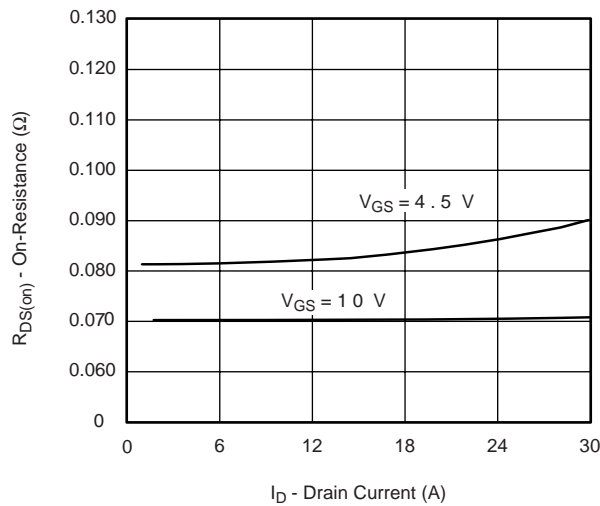
**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



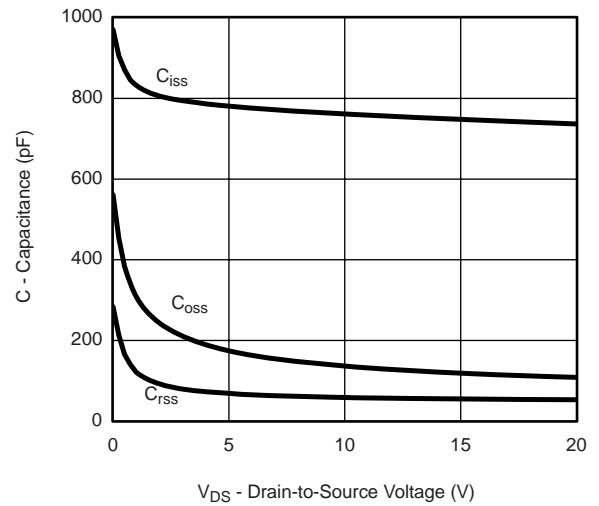
$V_{DS}$  - Drain-to-Source Voltage (V)  
**Output Characteristics**



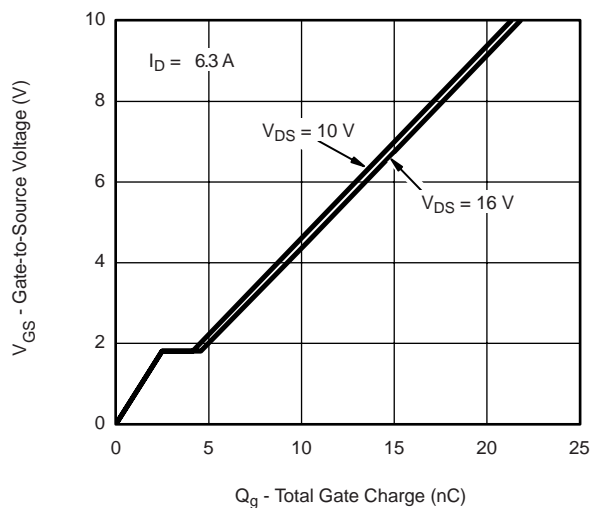
$V_{GS}$  - Gate-to-Source Voltage (V)  
**Transfer Characteristics**



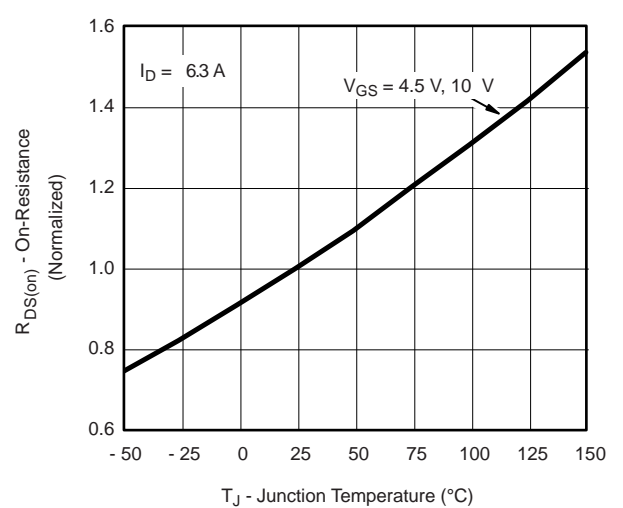
$I_D$  - Drain Current (A)  
**On-Resistance vs. Drain Current**



$V_{DS}$  - Drain-to-Source Voltage (V)  
**Capacitance**

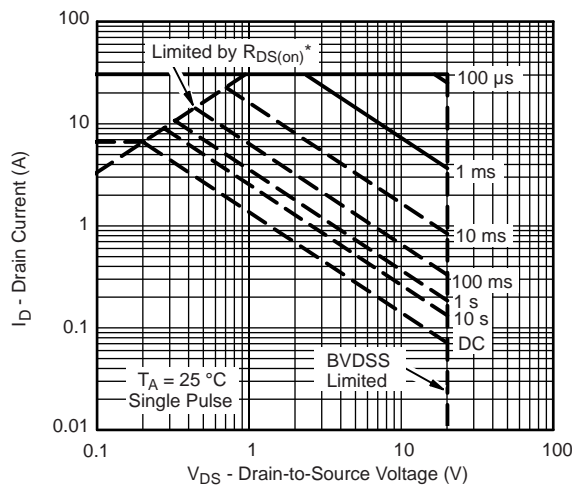
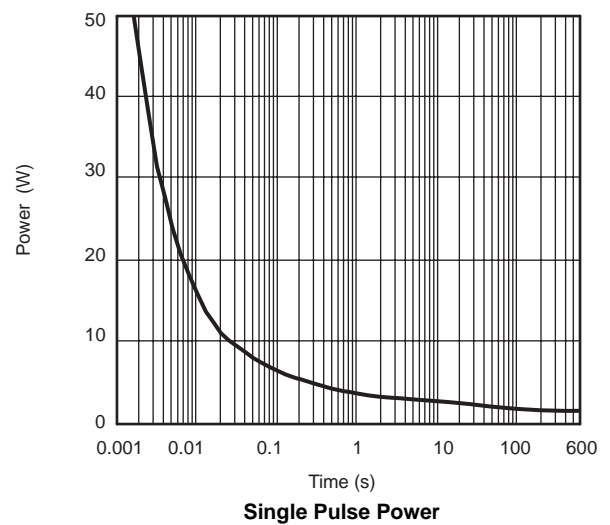
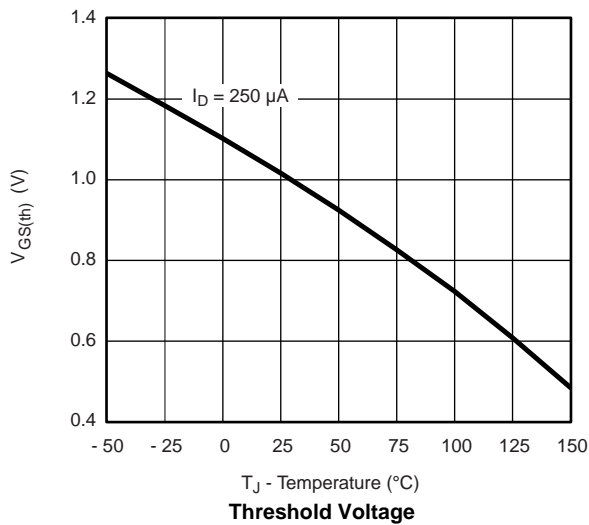
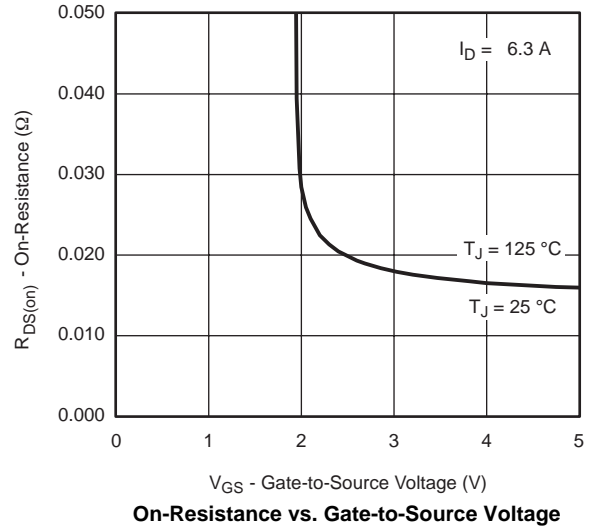
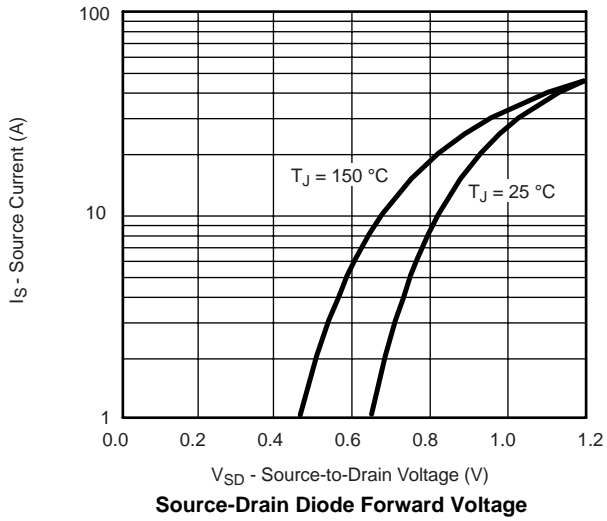


$Q_g$  - Total Gate Charge (nC)  
**Gate Charge**



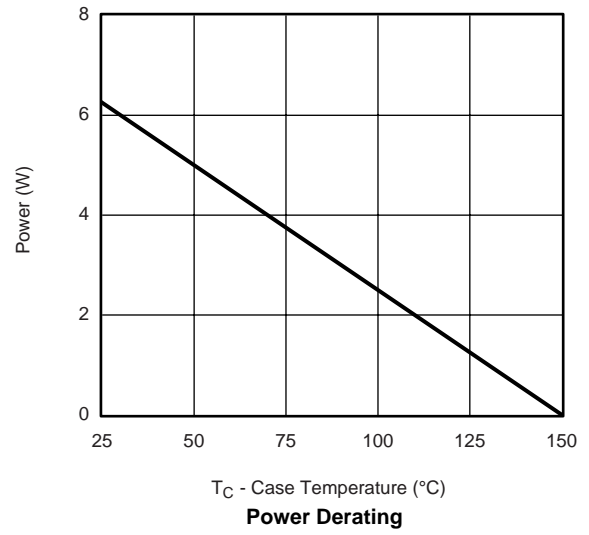
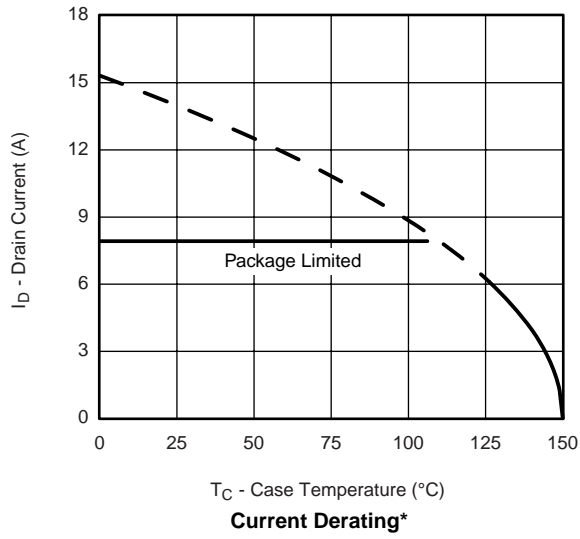
$T_J$  - Junction Temperature ( $^\circ\text{C}$ )  
**On-Resistance vs. Junction Temperature**

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



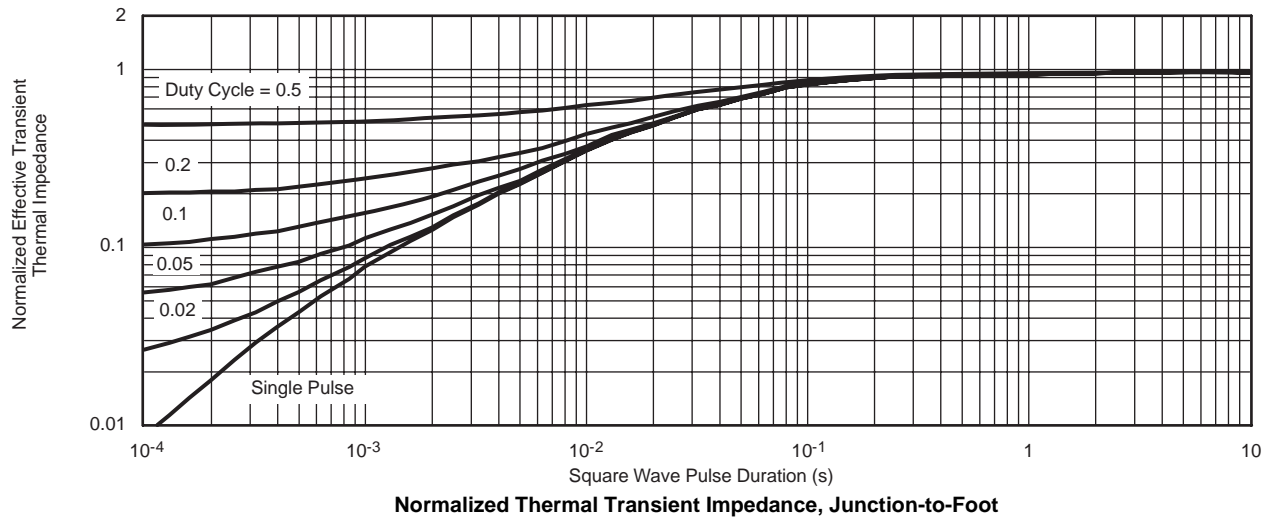
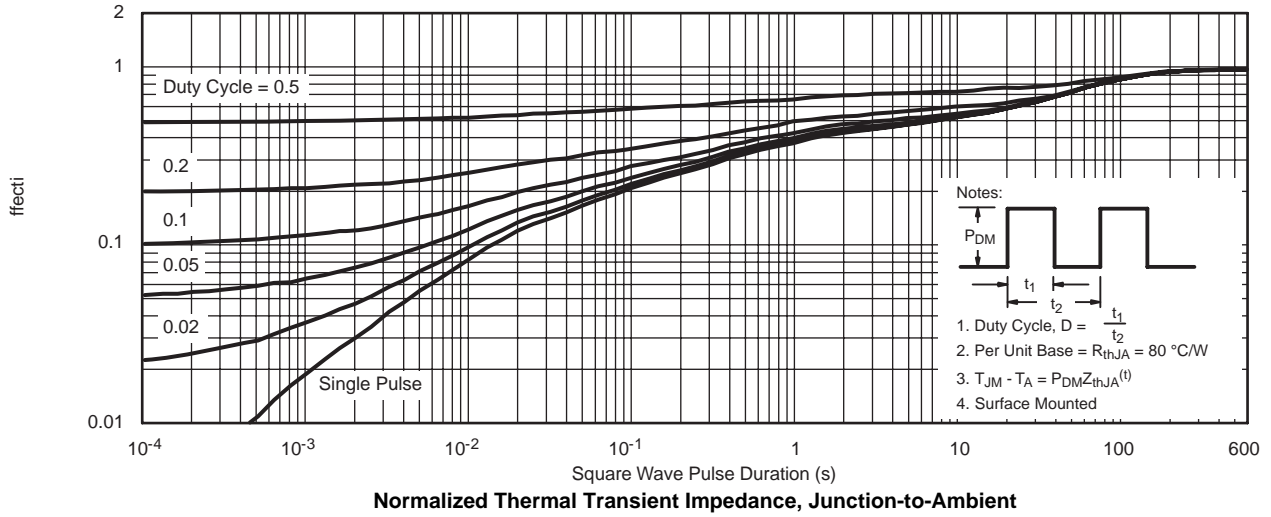
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



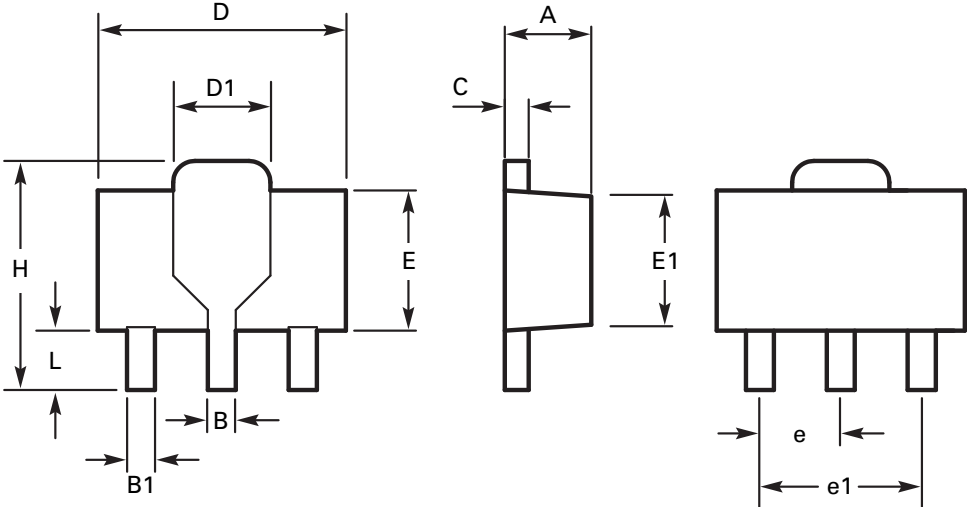
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150\text{ °C}$ , using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



# RJP020N06T100-VB

## Package outline - SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.62	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

**Note:** Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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